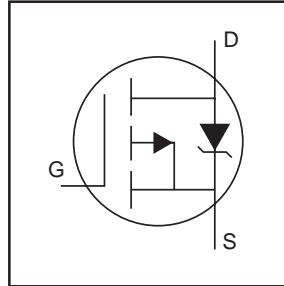


- Ultra Low On-Resistance
- Surface Mount (IRFR5305)
- Straight Lead (IRFU5305)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

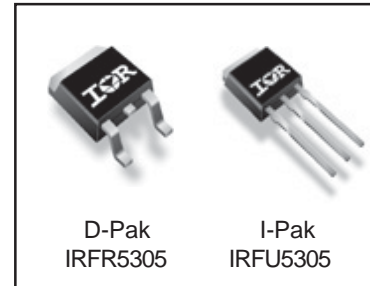


$V_{DSS} = -55V$
$R_{DS(on)} = 0.065\Omega$
$I_D = -31A$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



D-Pak
IRFR5305

I-Pak
IRFU5305

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-31	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-22	
I_{DM}	Pulsed Drain Current ①②	-110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②③	280	mJ
I_{AR}	Avalanche Current ①③	-16	A
E_{AR}	Repetitive Avalanche Energy ①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③④	-5.0	V/ns
T_J	Operating Junction and Storage Temperature Range	-55 to + 175	°C
T_{STG}			
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	50	
$R_{\theta JA}$	Junction-to-Ambient**	—	110	

IRFR/U5305PbF

International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
	$V_{(BR)DSS}$	-55	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
	$\Delta V_{(BR)DSS}/\Delta T_J$	—	-0.034	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
	$R_{DS(on)}$	—	—	0.065	Ω	$V_{GS} = -10V, I_D = -16A$ ④
	$V_{GS(th)}$	-2.0	—	-4.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
	g_{fs}	8.0	—	—	S	$V_{DS} = -25V, I_D = -16A$ ⑥
	I_{DSS}	—	—	-25	μA	$V_{DS} = -55V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
	I_{GSS}	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
	Q_g	—	—	63	nC	$I_D = -16A$
	Q_{gs}	—	—	13		$V_{DS} = -44V$
	Q_{gd}	—	—	29		$V_{GS} = -10V$, See Fig. 6 and 13 ④⑥
	$t_{d(on)}$	—	14	—	ns	$V_{DD} = -28V$ $I_D = -16A$ $R_G = 6.8\Omega$ $R_D = 1.6\Omega$, See Fig. 10 ④⑥
	t_r	—	66	—		
	$t_{d(off)}$	—	39	—		
	t_f	—	63	—		
	L_D	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑤
	L_S	—	7.5	—		
	C_{iss}	—	1200	—	pF	$V_{GS} = 0V$ $V_{DS} = -25V$ $f = 1.0\text{MHz}$, See Fig. 5 ⑥
	C_{oss}	—	520	—		
	C_{rss}	—	250	—		

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
	I_S	—	—	-31	A	MOSFET symbol showing the integral reverse p-n junction diode.
	I_{SM}	—	—	-110		
	V_{SD}	—	—	-1.3	V	$T_J = 25^\circ\text{C}, I_S = -16A, V_{GS} = 0V$ ④
	t_{rr}	—	71	110	ns	$T_J = 25^\circ\text{C}, I_F = -16A$
	Q_{rr}	—	170	250	nC	$di/dt = -100A/\mu s$ ④⑥

Notes:

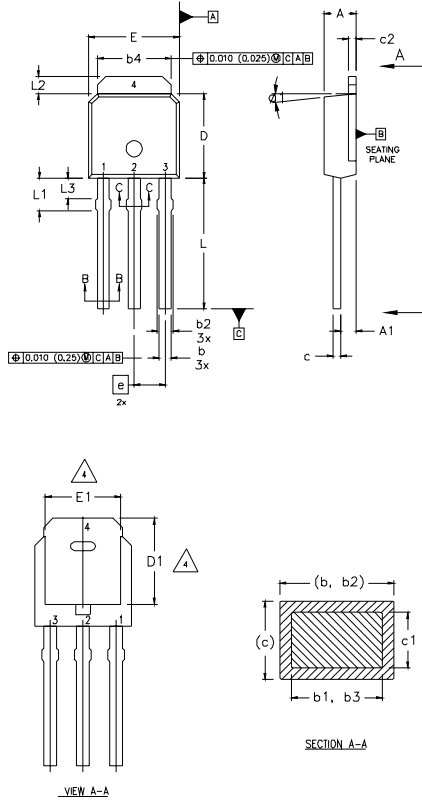
- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② $V_{DD} = -25V$, starting $T_J = 25^\circ\text{C}$, $L = 2.1\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = -16A$. (See Figure 12)
- ③ $I_{SD} \leq -16A$, $di/dt \leq -280A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
- ⑥ Uses IRF5305 data and test conditions.

* When mounted on 1" square PCB (FR-4 or G-10 Material).
 For recommended footprint and soldering techniques refer to application note #AN-994.

** Uses typical socket mount.

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	Ø	15°	Ø	15°	

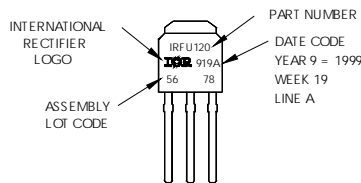
LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"
Note: "P" in assembly line
position indicates "Lead-Free"



OR

